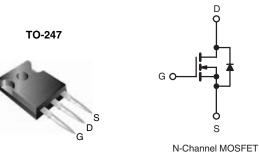


Power MOSFET

PRODUCT SUMMA	RY		
V _{DS} (V)	500		
R _{DS(on)} (Ω)	V _{GS} = 10 V	0.40	
Q _g (Max.) (nC)	6	4	
Q _{gs} (nC)	1	6	
Q _{gd} (nC)	2	6	
Configuration	Sin	igle	



FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Pb
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective Coss Specified
- Lead (Pb)-free Available

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptable Power Supply
- High Speed Power Switching

TYPICAL SMPS TOPOLOGIES

- Two Transistor Forward
- Half Bridge, Full Bridge
- PFC Boost

ORDERING INFORMATION	
Package	TO-247
Lead (Pb)-free	IRFP450APbF
Lead (FD)-liee	SiHFP450A-E3
SnPb	IRFP450A
	SiHFP450A

ABSOLUTE MAXIMUM RATINGS T	_C = 25 °C, u	nless otherw	vise noted		
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	500	V
Gate-Source Voltage		V _{GS}	± 30	- V	
Continuous Drain Current	V _{GS} at 10 V	$T_{C} = 25 \text{ °C}$ $T_{C} = 100 \text{ °C}$		14	
Continuous Drain Current	VGS at 10 V	T _C = 100 °C	I _D	8.7	A
Pulsed Drain Current ^a	•	•	I _{DM}	56	
Linear Derating Factor				1.5	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	760	mJ
Repetitive Avalanche Current ^a			I _{AR}	14	A
Repetitive Avalanche Energy ^a			E _{AR}	19	mJ
Maximum Power Dissipation	T _C =	25 °C	PD	190	W
Peak Diode Recovery dV/dt ^c	•		dV/dt	4.1	V/ns
Operating Junction and Storage Temperature Rang	e		T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for	10 s	-	300 ^d	7
Mounting Torque	6.00.01	V3 screw		10	lbf ⋅ in
Mounting Torque	6-32 OF I	við screw		1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Starting T_J = 25 °C, L = 7.8 mH, R_G = 25 Ω , I_{AS} = 14 A (see fig. 12).

c. $I_{SD} \leq 14$ A, $dI/dt \leq 130$ A/µs, $V_{DD} \leq V_{DS}, \, T_J \leq 150 \ ^{\circ}C.$

d. 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply



THERMAL RESISTANCE RA	TINGS							
PARAMETER	SYMBOL	TYP. MAX.				UNIT		
Maximum Junction-to-Ambient	R _{thJA}	- 40 0.24 -						
Case-to-Sink, Flat, Greased Surface	R _{thCS}				°C/W			
Maximum Junction-to-Case (Drain)	R _{thJC}	-	- 0.65		-			
SPECIFICATIONS $T_J = 25 \degree C$,	unless otherv	vise noted						
PARAMETER	SYMBOL		CONDITI	ONS	MIN.	TYP.	MAX.	UNIT
Static							I	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$) V, I _D = 2	50 µA	500	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference	to 25 °C,	I _D = 1 mA	-	0.58	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V$	′ _{GS} , I _D = 2	250 μΑ	2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	VG	$_{is} = \pm 30$	V	-	-	± 100	nA
		V _{DS} = 5	00 V, V _{GS}	s = 0 V	-	-	25	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 400 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$		-	-	250	μA	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	Ic	₀ = 8.4 A ^b	-	-	0.40	Ω
Forward Transconductance	g _{fs}	V _{DS} = 5	0 V, I _D =	8.4 A ^b	7.8	-	-	S
Dynamic							I	
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	2038	-		
Output Capacitance	C _{oss}			-	307	-		
Reverse Transfer Capacitance	C _{rss}			-	10	-		
Output Capacitance	C _{oss}	V _{GS} = 0 V; V _D	_S = 1.0 V,	f = 1.0 MHz		2859		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V; V _D	_S = 400 V	, f = 1.0 MHz		81		
Effective Output Capacitance	C _{oss} eff.	V _{GS} = 0 V;	V _{DS} = 0 V	' to 400 V ^c		96		
Total Gate Charge	Qg				-	-	64	
Gate-Source Charge	Q _{gs}	V _{GS} = 10 V		A, V _{DS} = 400 V, ig. 6 and 13 ^b	-	-	16	nC
Gate-Drain Charge	Q _{gd}		3661	ig. o and 15*	-	-	26	
Turn-On Delay Time	t _{d(on)}				-	15	-	
Rise Time	t _r	- 		- 14 A	-	36	-	- ns
Turn-Off Delay Time	t _{d(off)}	- v _{DD} = 2 R _G = 6.2 Ω, F	50 V, I _D = I _D = 17 Ω,	see fig. 10 ^b	-	35	-	
Fall Time	t _f				-	29	-	_
Drain-Source Body Diode Characteristic	cs						I	
Continuous Source-Drain Diode Current	١ _S	MOSFET symbol showing the			-	-	14	
Pulsed Diode Forward Currenta	I _{SM}	integral reverse p - n junction die			-	-	56	A
Body Diode Voltage	V _{SD}	T _J = 25 °C, I	_S = 14 A,	V _{GS} = 0 V ^b	-	-	1.4	V
Body Diode Reverse Recovery Time	t _{rr}		14 4 -11/	dt 100 4/b	-	487	731	ns
Body Diode Reverse Recovery Charge	Q _{rr}	– T _J = 25 °C, I _F =	14 A, al/(μι = 100 Α/μs ⁵	-	3.9	5.8	μC
Forward Turn-On Time	t _{on}	Intrinsic turn	-on time i	s negligible (turn	-on is dor	ninated b	y L _S and	L _D)

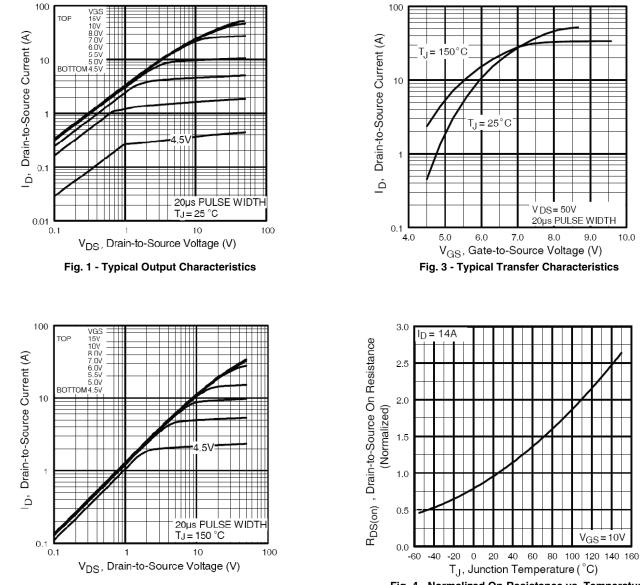
Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).

b. Pulse width \leq 300 µs; duty cycle \leq 2 %. c. C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80 % V_{DS}.



10.0



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Fig. 2 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

IRFP450A, SiHFP450A

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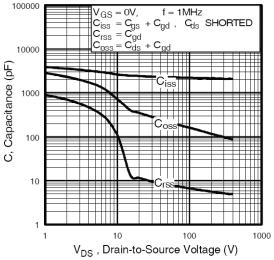
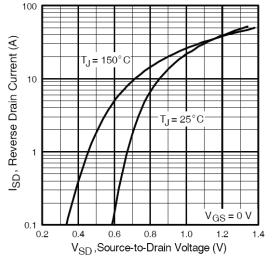


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



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Fig. 7 - Typical Source-Drain Diode Forward Voltage

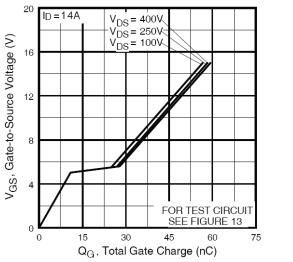
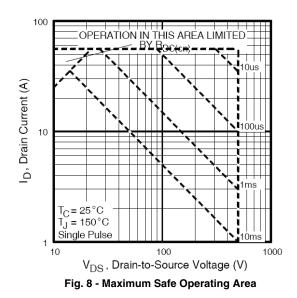
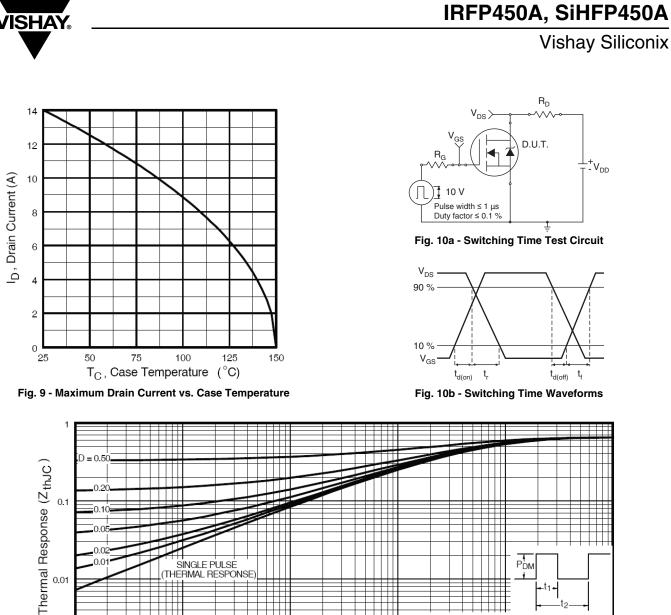
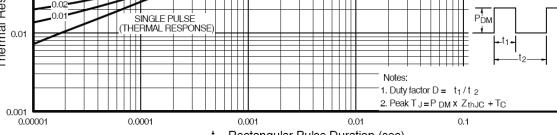
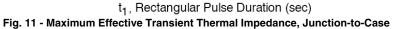


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage









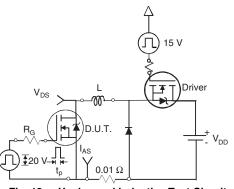


Fig. 12a - Unclamped Inductive Test Circuit

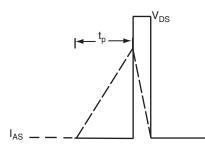


Fig. 12b - Unclamped Inductive Waveforms

IRFP450A, SiHFP450A

Vishay Siliconix



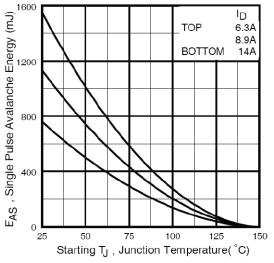


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

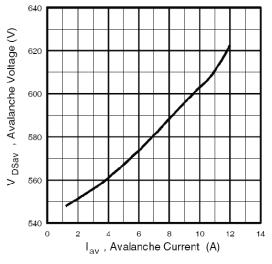


Fig. 12d - Typical Drain-to-Source Voltage vs. Avalanche Current

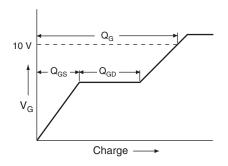


Fig. 13a - Basic Gate Charge Waveform

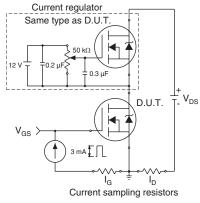
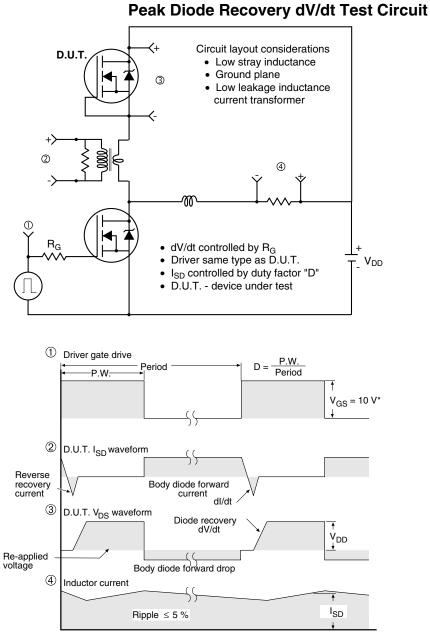


Fig. 13b - Gate Charge Test Circuit





* $V_{GS} = 5$ V for logic level devices

Fig. 14 - For N-Channel

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TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9





Section C--C, D--D, E--E

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
А	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØP	3.56	3.65	7
Ø P1	7.19) ref.	
Q	5.31	5.69	
S	5.54	5.74	

Notes

- ⁽¹⁾ Package reference: JEDEC[®] TO247, variation AC
- (2) All dimensions are in mm
- ⁽³⁾ Slot required, notch may be rounded
- ⁽⁴⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁵⁾ Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition



VERSION 2: FACILITY CODE = Y



	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
A	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØΡ	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51	BSC	

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- ⁽²⁾ Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- ⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c



VERSION 3: FACILITY CODE = N



MILLIMETERS		MILLIMETERS		MILLIN	IETERS
DIM.	MIN.	MAX.	DIM.	MIN.	MAX.
А	4.65	5.31	D2	0.51	1.35
A1	2.21	2.59	E	15.29	15.87
A2	1.17	1.37	E1	13.46	-
b	0.99	1.40	е	5.46	BSC
b1	0.99	1.35	k	0.:	254
b2	1.65	2.39	L	14.20	16.10
b3	1.65	2.34	L1	3.71	4.29
b4	2.59	3.43	N	7.62	BSC
b5	2.59	3.38	Р	3.56	3.66
С	0.38	0.89	P1	-	7.39
c1	0.38	0.84	Q	5.31	5.69
D	19.71	20.70	R	4.52	5.49
D1	13.08	-	S	5.51	BSC

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

⁽²⁾ Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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